DESCRIPTION

The 4419 is the P-Channel logic enhancement mode power field effect transistor is produced using high cell density advanced trench technology..
This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, notebook computer power management and other battery powered circuits where high-side switching

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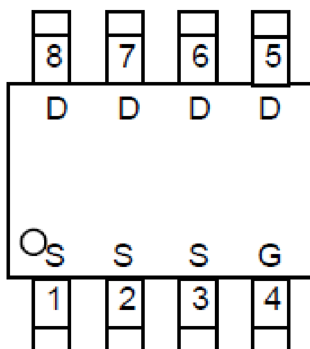
FEATURE

- ***-30V/-9.7A, $R_{DS(ON)}$=19.5mΩ (typ.)@V_{GS}=-10V***
- ***-30V/-7.0A, $R_{DS(ON)}$=23.5mΩ (typ.)@V_{GS}=-4.5V***
- Super high design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and Maximum DC current capability
- Full RoHS compliance
- SOP8 package design

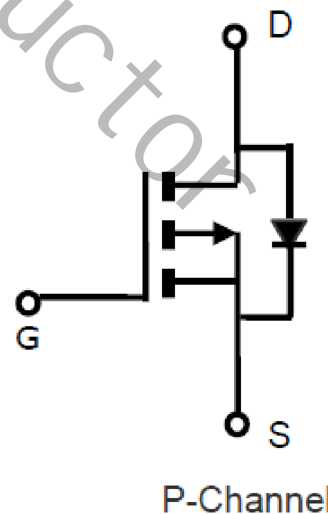
APPLICATIONS

- High Frequency Point-of-Load Synchronous
- Newworking DC-DC Power System
- Load Switch

PIN CONFIGURATION



TOP VIEW
SOP-8



P-Channel

■ ABSOLUTE MAXIMUM RATINGS *(T_A = 25℃ Unless otherwise noted)*

Symbol	Parameter		Typical	Unit
V_{DSS}	Drain-Source Voltage		-30	V
V_{GSS}	Gate-Source Voltage		±20	V
I_D	Continuous Drain Current (T_A=25℃)	V_{GS}=10V	-9.7	A
I_{DM}	Pulsed Drain Current		-40	A
I_S	Continuous Source Current (Diode Conduction)		-2.1	A
P_D	Power Dissipation	T_A=25℃	3.0	W
		T_A=70℃	2.1	
T_J	Operation Junction Temperature		150	℃
T_{STG}	Storage Temperature Range		-55~+150	℃
$R_{θJA}$	Thermal Resistance Junction to Ambient		85	℃/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress rating only and functional device operation is not implied

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■ *ELECTRICAL CHARACTERISTICS(T_A=25℃ Unless otherwise noted)*

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Parameters						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-30			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-1.2	-1.4	-2.7	V
I_{GSS}	Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0			-1	uA
		V_{DS}=-24V, V_{GS}=0 T_J=55℃			-5	
$R_{DS(ON)}$	Drain-Source On-Resistance	V_{GS}=-10V, I_D=-9.7A		19.5	28	mΩ
		V_{GS}=-4.5V, I_D=-7A		23	35	
Source-Drain Diode						
V_{SD}	Diode Forward Voltage	I_S=-1.0A, V_{GS}=0V		-0.7	-1.0	V
Dynamic Parameters						
Q_g	Total Gate Charge	V_{DS}=-15V V_{GS}=-10V I_D=-9.7A		33.82	43.97	nC
Q_{gs}	Gate-Source Charge			4.93	6.41	
Q_{gd}	Gate-Drain Charge			5.2	6.76	
C_{iss}	Input Capacitance	V_{DS}=-15V V_{GS}=0V f=1MHz		1573	1900	pF
C_{oss}	Output Capacitance			319		
C_{rss}	Reverse Transfer Capacitance			211	295	
$T_{d(on)}$	Turn-On Time	V_{DS}=-15V I_D=-10A V_{GEN}=-10V R_G=6Ω		15.44	30.88	nS
T_r				5.04	10.08	
$T_{d(off)}$	Turn-Off Time			71.04	142.08	
T_f				16.8	33.6	

Note: 1. Pulse test: pulse width<=300uS, duty cycle<=2%

2.Static parameters are based on package level with recommended wire bonding

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■ *TYPICAL CHARACTERISTICS (25℃ Unless Note)*

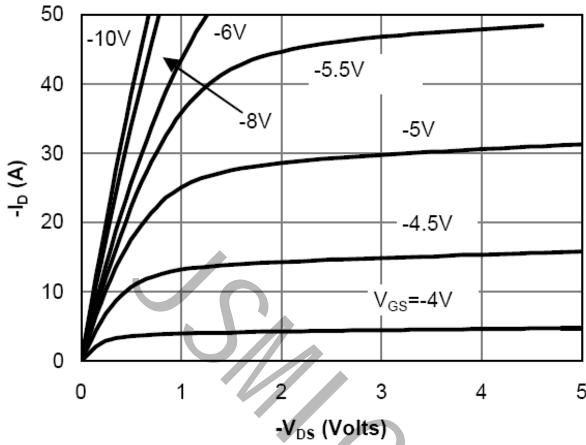

Fig 1: On-Region Characteristics

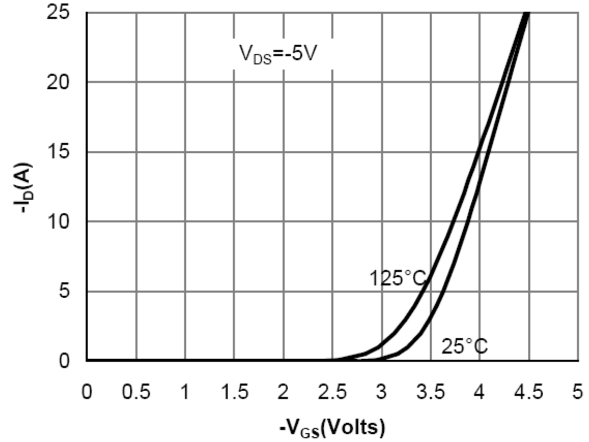

Figure 2: Transfer Characteristics

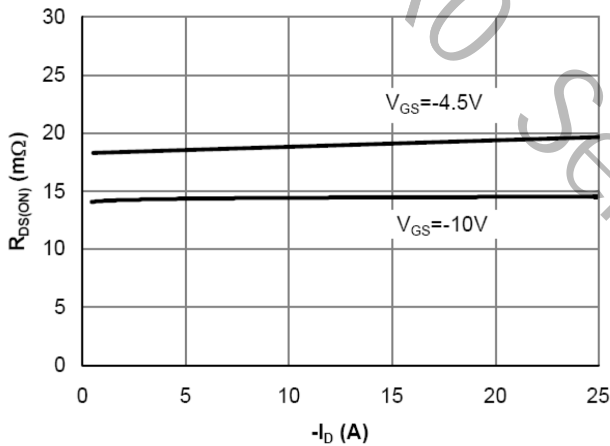

Figure 3: On-Resistance vs. Drain Current and Gate Voltage

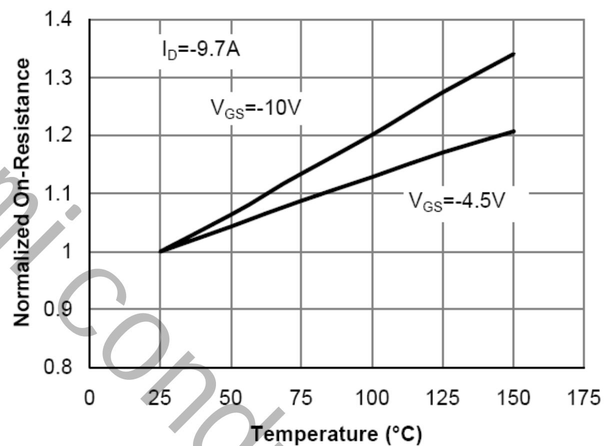

Figure 4: On-Resistance vs. Junction Temperature

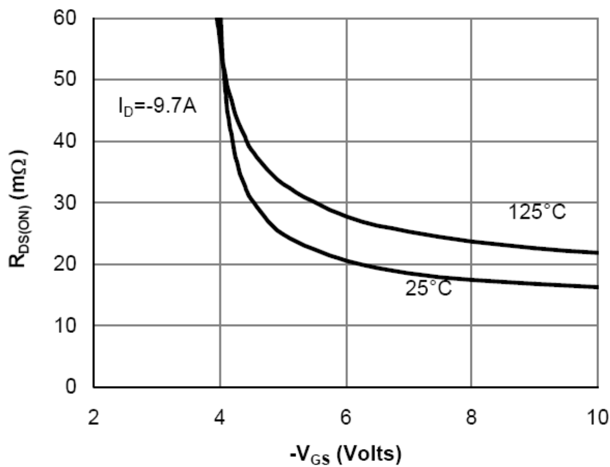

Figure 5: On-Resistance vs. Gate-Source Voltage

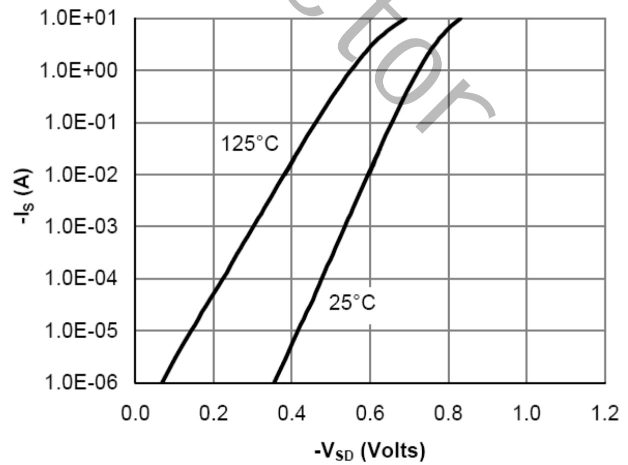

Figure 6: Body-Diode Characteristics

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■ *TYPICAL CHARACTERISTICS (continuous)*

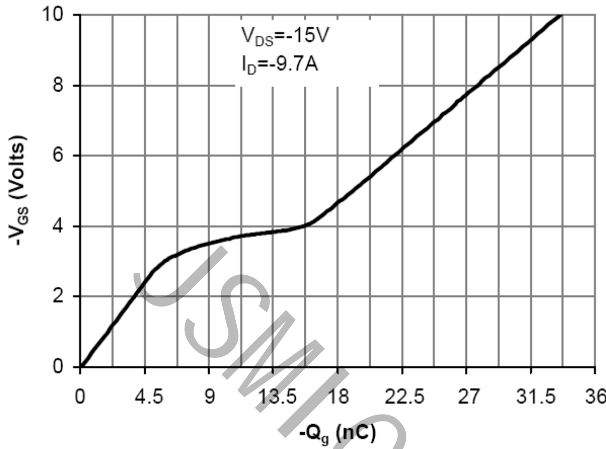

Figure 7: Gate-Charge Characteristics

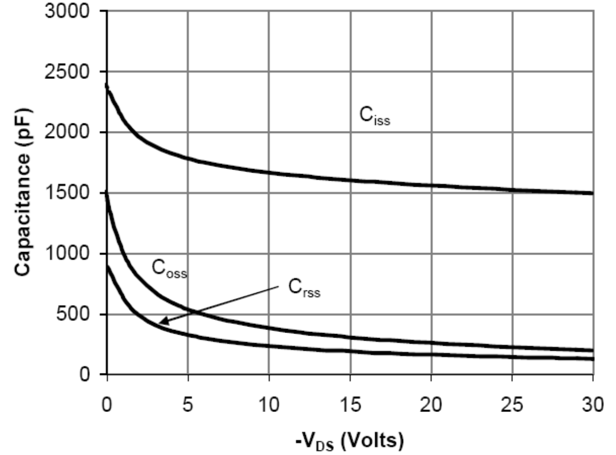

Figure 8: Capacitance Characteristics

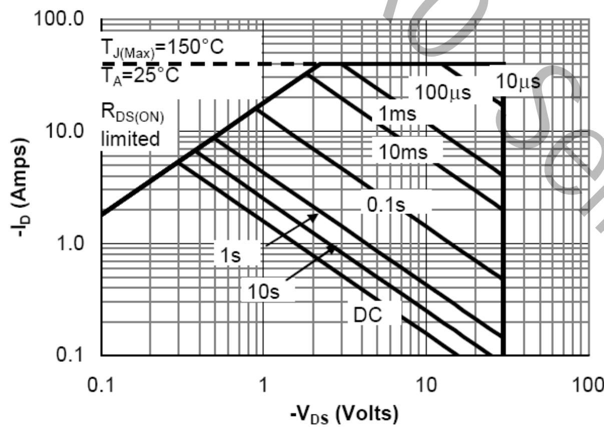

Figure 9: Maximum Forward Biased Safe Operating Area

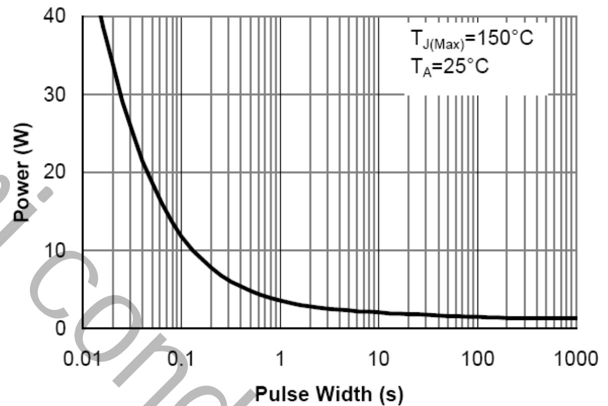

Figure 10: Single Pulse Power Rating Junction-to-Ambient

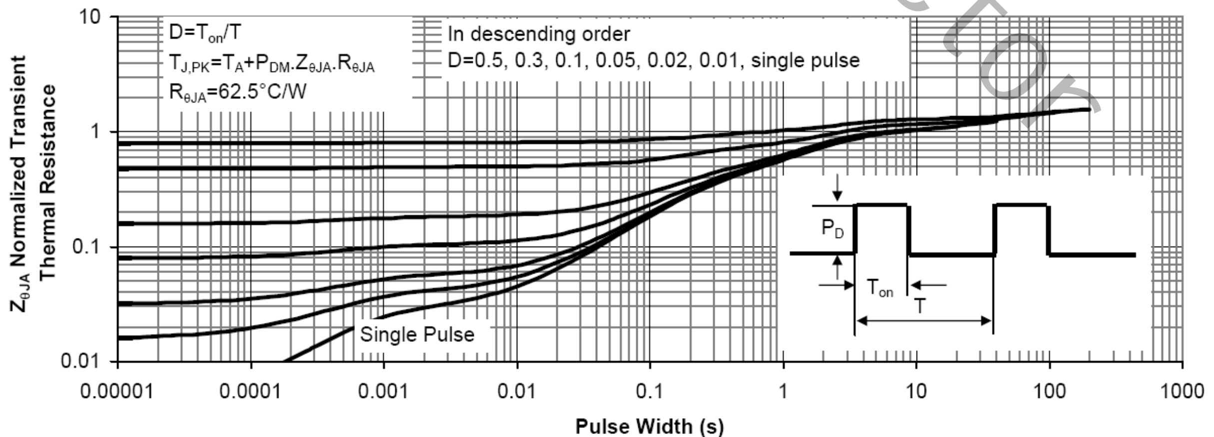

Figure 11: Normalized Maximum Transient Thermal Impedance

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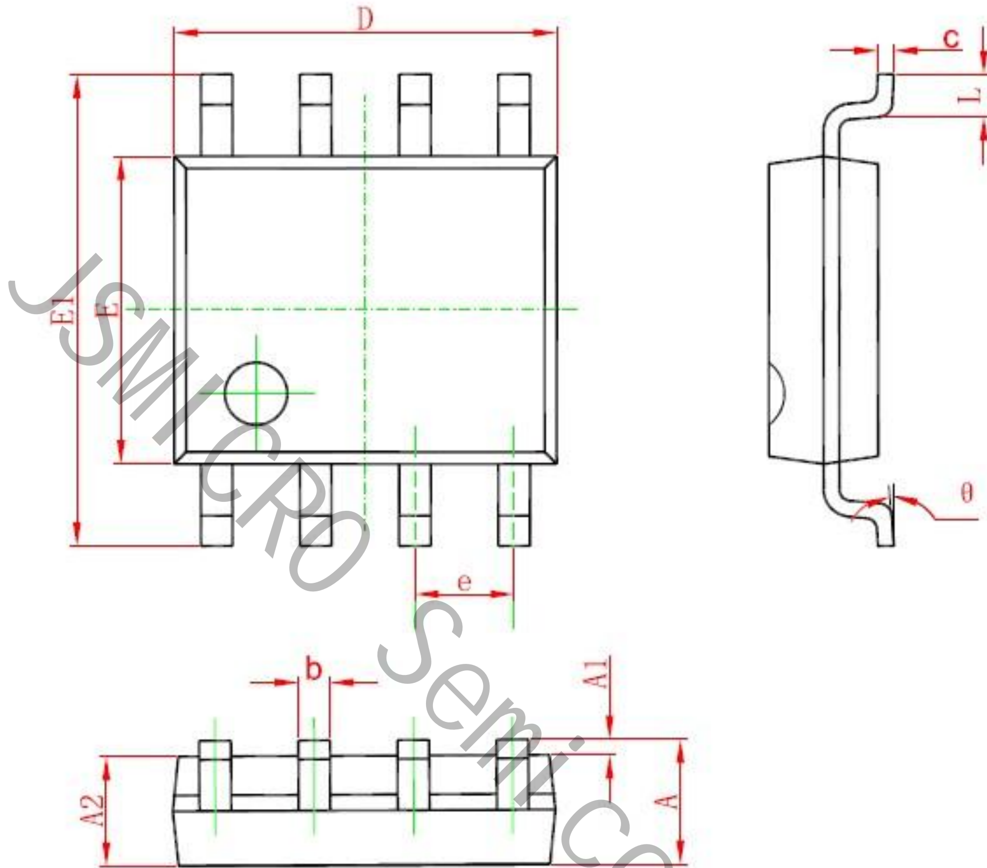
■ *SOP8 PACKAGE OUTLINE DIMENSIONS*



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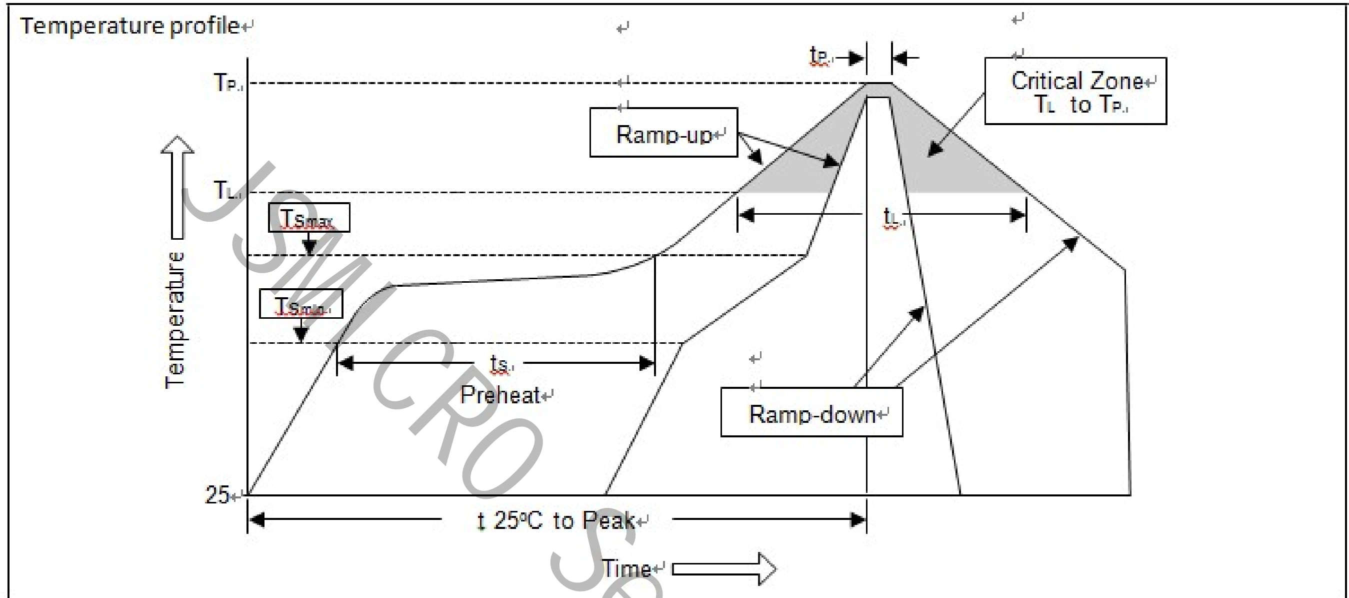
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

■ *SOLDERING METHODS FOR UNIVERCHIP*

Storage environment Temperature=10℃~35℃ Humidity=65%±15%

Reflow soldering of surface mount device



Profile Feature	Sn-Pb Eutectic Assembly	Pb free Assembly
Average ramp-up rate (T_L to T_P)	<3℃/sec	<3℃/sec
Preheat -Temperature Min (Ts_{min}) -Temperature Max (Ts_{max}) -Time (min to max) (ts)	100℃ 150℃ 60~120 sec	150℃ 200℃ 60~180 sec
Tsmax to T_L -Ramp-up Rate	<3℃/sec	<3℃/sec
Time maintained above -Temperature (T_L) -Time (t_L)	183℃ 60~150 sec	217℃ 60~150 sec
Peak Temperature (T_P)	240℃+0/-5℃	260℃+0/-5℃
Time within 5℃ of actual Peak Temperature (t_P)	10~30 sec	20~40 sec
Ramp-down Rate	<6℃/sec	<6℃/sec
Time 25℃ to Peak Temperature	<6 minutes	<6 minutes

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